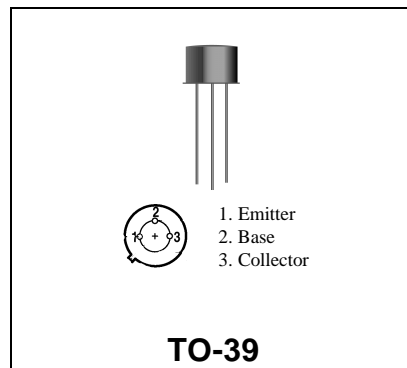


MRF586

**RF & MICROWAVE DISCRETE
 LOW POWER TRANSISTORS**

Features

- Silicon NPN, To-39 packaged VHF/UHF Transistor
- $f_{tau} = 3.0 \text{ GHz (typ) @ } 300\text{MHz, } 14\text{v, } 90\text{mA,}$
- $G_{U \text{ max}} = 12.5\text{dB (typ) @ } 300 \text{ MHz, } 15\text{v, } 40\text{mA}$
- $|S_{21}|^2 = 12.5\text{dB (typ) @ } 300 \text{ MHz, } 15\text{v, } 40\text{mA}$



DESCRIPTION:

Silicon NPN transistor, designed for VHF and UHF equipment. Applications include amplifier; pre-driver, driver, and output stages. Also suitable for oscillator and frequency-multiplier functions.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter	20	Vdc
V_{CBO}	Collector-Base Voltage	35	Vdc
V_{EBO}	Emitter-Base Voltage	3.0	Vdc
I_C	Collector Current	200	mA

Thermal Data

P_D	Total Device Dissipation @ $T_A = 25^{\circ}\text{C}$ Derate above 25°C	1.0 5.71	Watts mW/ $^{\circ}\text{C}$
-------	--	-------------	---------------------------------

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC
 (off)

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BVCEO	Collector-Emitter Breakdown Voltage (IC = 5.0 mAdc)	20	-	-	Vdc
BVEBO	Emitter-Base Breakdown Voltage (IC = 0.1 mAdc)	3.0	-	-	Vdc
BVCBO	Collector-Base Breakdown Voltage (IC = 1.0 mAdc)	30	-	-	Vdc
ICBO	Collector-Base (VCB = 10 Vdc)	-	50	-	μA

(on)

HFE	DC Current Gain (IC = 50 mAdc, VCE = 5.0 Vdc)	50	-	200	-
-----	--	----	---	-----	---

DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
f _T	Current-Gain - Bandwidth Product (IC = 90 mAdc, VCE = 14 Vdc, f = 300 MHz)	-	3.0	-	GHz
CCB	Collector Base Capacitance VCB = 10V, IE = o, f = 1.0MHz		3.0		pF

MRF586

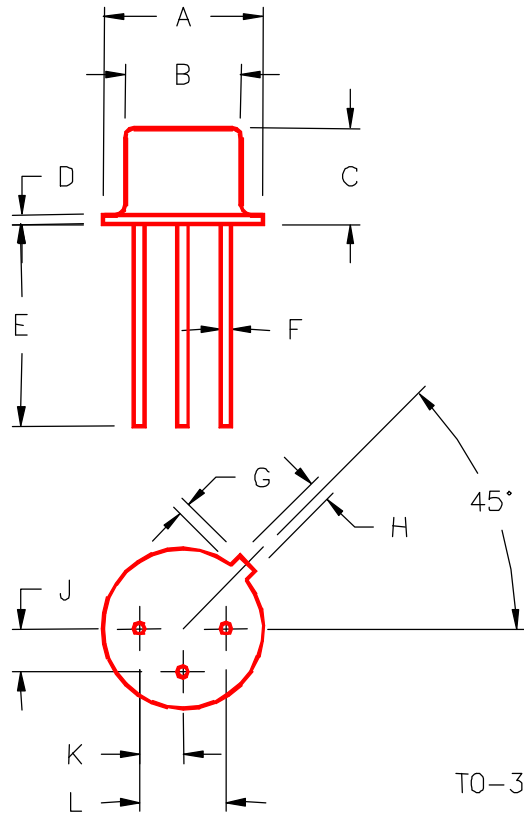
FUNCTIONAL

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
$G_{U \max}$	Maximum Unilateral Gain (1)	IC = 40 mAdc, VCE = 15Vdc, f = 300 MHz	-	12.5	-	dB
MAG	Maximum Available Gain	IC = 40 mAdc, VCE = 15Vdc, f = 300 MHz	-	13.5	-	dB
$ S_{21} ^2$	Insertion Gain	IC = 40 mAdc, VCE = 15Vdc, f = 300 MHz	10	11.5	-	dB

Table 1. Common Emitter S-Parameters, @ VCE = 15 V, IC = 40 mA

f (MHz)	S11		S21		S12		S22	
	S11	$\angle \phi$	S21	$\angle \phi$	S12	$\angle \phi$	S22	$\angle \phi$
100	.096	107	10.28	103	.053	84	.479	-40
200	.129	114	5.58	89	.104	83	.361	-49
300	.165	108	3.94	79	.160	76	.356	-56
400	.185	115	3.04	71	.192	74	.388	-71
500	.237	115	2.64	67	.246	75	.384	-79
600	.247	112	2.42	60	.288	71	.408	-82
700	.247	113	2.26	54	.326	69	.417	-84
800	.238	118	2.06	48	.334	67	.432	-87
900	.260	119	1.97	47	.369	71	.420	-91
1000	.246	116	2.06	43	.405	67	.444	-92

PACKAGE STYLE M246



T0-39

	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.350/8,89	.370/9,40	J	.095/2,41	.105/2,67
B	.315/8,00	.335/8,51	K	.095/2,41	.105/2,67
C	.240/6,10	.260/6,60	L	.190/4,83	.210/5,33
D	.015/0,38	.045/1,14			
E	.500/12,70				
F	.016/0,41	.019/0,48			
G	.029/0,74	.040/1,02			
H	.028/0,71	.034/0,86			